

## **MOLD TYPE BIPOLAR TRANSISTORS** Ratings and Specifications

查询"2SB1532"供应商

## General use transistors

- Can be available to general applications
- · Designed for complementary use

Device type	V <sub>сво</sub> Volts	V <sub>CEO</sub>	V <sub>CEO</sub> (sus) Volts	lc cont. Amps.	Pc Watts	hee min.	lc Amps.	Vce	Switcl ton µsec.	ning tim t <sub>stg</sub> μsec.	tr usec.		Net mass Grams	Equivalent circuit Page 31
2SD847	40	40	40	15	100	40	5	5		_	_	TO-3P	6	
2SB757	-40	-40	-40	-15	100	40	-5	-5				TO-3P	6	
2SD1.117	40	40	40	10	50	40	2	5			_	TO-220AB	2	
2SB850 #	-40	-40	-40	-10	50	40	-2	-5		_	-	TO-220AB	2	
2SB1532	-40	-40	-40	-10	40	40	-2	-5		_	_	TO-220F17	2.5	
2SB862	-120	-80	-80	-5	30	1000	-1	-5	_			TO-220AB	2	
ET367	-120	-80	-80	-5	30	1000	-1	-5	_		_	TO-220F17	2.5	Fig. B1
2SD1157	80	50	50	4	25	250	0.5	5	0.5	3.0	0.8	TO-220AB	2	_

## Building block transistors

Suitable for motor control applicationsHigh voltage, high current capacity

VCEO: 300 – 600V, Ic: 100 – 500A
Easily connected in parallel and control currents up to 1200A

Device type	Vсво	Vceo	VcEo.	lc .	Pc = "	"ħFE"	· 量聚产工业	440	Switch		e (Max.)	Package		Equivalent
	Volts	Volts	(sus) Volts	cont. Amps.	Watts	min,	Amps.	V <sub>CE</sub> Volts	ton # # ⊭µsec.	usec.	tr μsec.		mass Grams	Page 31
1D200A-020	300	300	250	200	800	100	200	5	2.0	12	3.0	BBT II	145	Fig. B6
1D500A-030	400	400	300	500	2000	500	500	2	2.0	12	4	BBT IV	365	Fig. B11
ET188	400	400	300	100	600	200	100	5	2.0	12.0	3.0	BBT II	145	Fig. B3
ETN35-030	400	400	300	300	1500	150	300	5	2.0	12.0	1.2	BBT III	270	_
ETM36-030	400	400	320	200	1000	150	200	5	2.0	10.0	1.2	BBT III	270	Fig. B4
ETN36-030	400	400	320	300	1500	150	300	5	2.0	10.0	1.2	BBT Ⅲ	270	Fig. B4
ET127	600	600	450	100	770	100	100	5	4.0	10.0	3.0	BBT I	200	Fig. B9
ETN01-055	600	600	550	200	1500	8	120	5	2.0	8.0	2.0	BBT III	270	Fig. A1
ETN31-055	600	600	550	200	1500	70	200	5	2.0	12.0	3.0	BBT III	270	Fig. B9